



# Bipolar NPN Bare Die – BTN132

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## Part Description

The BTN132 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

## Key Parameters:

- VCBO = 80V
- VCEO = 75V
- VEBO = 7V
- hFE = 30-130 @ VCE = 4V, IC = 0.5A
- VCE(Sat) = 0.5V @ IC = 3A, IB = 100mA
- fT = 50 MHz @ VCE = 4V, IE = 0A
- COBO = - pF @ VCB = - V

## Features

Low VCE(sat). Designed to provide performance equivalent to BSS15

## Die Size (Unawn)

1020 $\mu$ m X 1020 $\mu$ m, 40 Mils X 40 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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